



60V N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max T _A = +25°C
60V	5Ω @ V _{GS} = 10V	210mA

Description and Applications

This MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- Motor Control
- Power Management Functions

Features

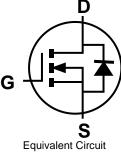
- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

Mechanical Data

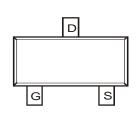
- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish Annealed over Alloy 42 Leadframe. Solderable per MIL-STD-202, Method 208 (e3)
- Terminal Connections: See Diagram
- Weight: 0.009 grams (Approximate)











Top View

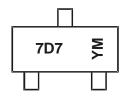
Ordering Information (Note 4)

Part Number	Case	Packaging
DMN67D7L-7	SOT23	3,000/Tape & Reel
DMN67D7L-13	SOT23	10,000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green"
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/

Marking Information



7D7 = Product Type Marking Code YM = Date Code Marking Y or \overline{Y} = Year (ex: E = 2017) M = Month (ex: 9 = September)

Date Code Key

Year	2015		2016	2017		2018	2019		2020	2021		2022
Code	С		D	E		F	G		Н	- 1		J
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



Maximum Ratings $(@T_A = +25^{\circ}C, \text{ unless otherwise specified.})$

Characteristic		Symbol	Value	Unit
Drain-Source Voltage	V_{DSS}	60	V	
Gate-Source Voltage	V_{GSS}	±40	V	
Continuous Drain Current (Note 6) V _{GS} = 10V	I _D	210 150	mA	
Maximum Body Diode Forward Current (Note 6)		Is	500	mA
Pulsed Drain Current (10µs Pulse, Duty Cycle = 19	I _{DM}	800	mA	

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

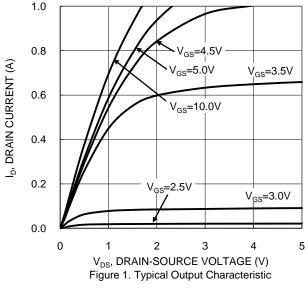
Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)		P_{D}	340	mW
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	R _{0JA}	376	°C/W
Total Power Dissipation (Note 6)		P_{D}	570	mW
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	$R_{\theta JA}$	224	°C/W
Operating and Storage Temperature Range		$T_{J,}T_{STG}$	-55 to +150	°C

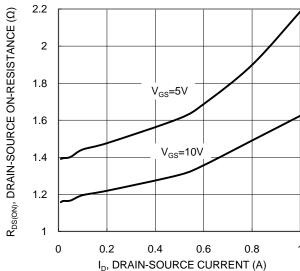
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)	- Cymbo.		. , , ,	max	1 0	i our containen	
Drain-Source Breakdown Voltage	BV _{DSS}	60	_	_	V	$V_{GS} = 0V, I_{D} = 10\mu A$	
Zero Gate Voltage Drain Current	I _{DSS}	_	_	1.0	μA	V _{DS} = 60V, V _{GS} = 0V	
Gate-Source Leakage	I _{GSS}	_	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	V _{GS(TH)}	0.8	_	2.5	V	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	
Static Drain-Source On-Resistance	D		3.2	7.5	Ω	$V_{GS} = 5.0V, I_D = 0.05A$	
Static Drain-Source On-Resistance	R _{DS(ON)}		1.5	5.0	5.2	$V_{GS} = 10V, I_D = 0.5A$	
Diode Forward Voltage	V _{SD}	_	0.78	1.5	V	V _{GS} = 0V, I _S = 115mA	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	C _{iss}	_	22	_	pF	.,	
Output Capacitance	Coss		4.1	_	рF	$V_{DS} = 25V, V_{GS} = 0V,$ f = 1.0MHz	
Reverse Transfer Capacitance	C _{rss}	_	2.5	_	pF		
Gate Resistance	Rg	_	120	_	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz$	
Total Gate Charge (V _{GS} = 4.5V)	Qg	_	361	_		V _{DS} = 10V, I _D = 250mA	
Total Gate Charge (V _{GS} = 10V)	Qg	_	821	_	Dα		
Gate-Source Charge	Q _{gs}	_	162	_	рС		
Gate-Drain Charge	Q_{gd}	_	116	_			
Turn-On Delay Time	t _{D(ON)}	_	2.8	_		V 00V I 0.0A	
Turn-On Rise Time	t _R	_	3.0	_	1	$V_{DD} = 30V, I_D = 0.2A,$	
Turn-Off Delay Time	t _{D(OFF)}	_	7.6	_	ns	$R_L = 150\Omega$, $V_{GEN} = 10V$,	
Turn-Off Fall Time	t _F	_	5.6	_		$R_{GEN} = 25\Omega$	

- 5. Device mounted on FR-4 PCB, with minimum recommended pad layout.
- 6. Device mounted on 1" x 1" FR-4 PCB with high coverage 2oz. Copper, single sided.
 7. Short duration pulse test used to minimize self-heating effect.
- 8. Guaranteed by design. Not subject to product testing.







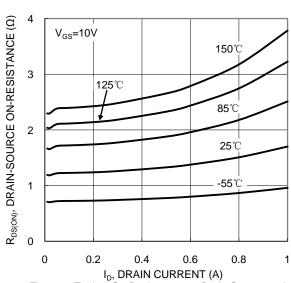
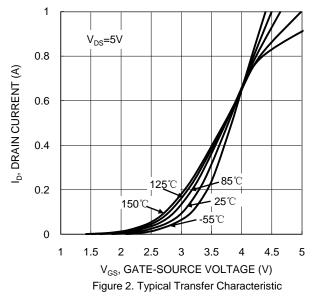


Figure 3. Typical On-Resistance vs. Drain Current and

Gate Voltage

Figure 5. Typical On-Resistance vs. Drain Current and Junction Temperature



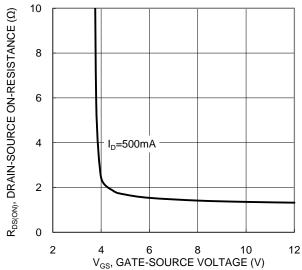


Figure 4. Typical Transfer Characteristic

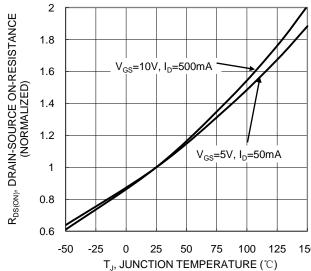


Figure 6. On-Resistance Variation with Junction Temperature



150

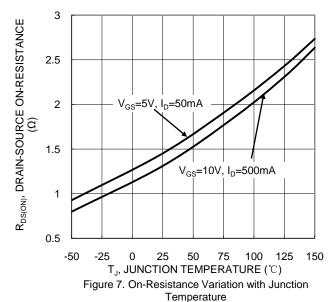


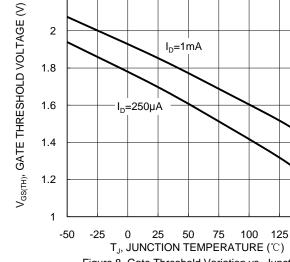
0.6

0.4

0.2

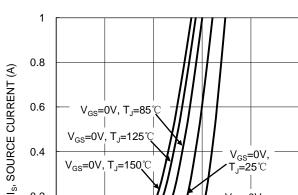
0 0





2.2

2



 $V_{GS}=0V, T_J=85$

 $V_{GS}=0V, T_J=125^{\circ}$

V_{GS}=0V, T_J=150°

0.3



 $V_{GS}=0V$,

_=25°C

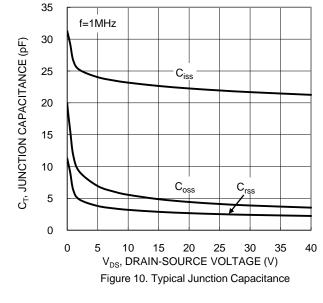
V_{GS}=0V,

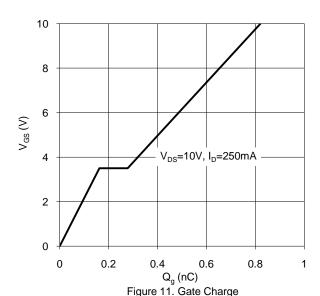
Γ_J=-55℃

1.2

Figure 8. Gate Threshold Variation vs. Junction Temperature

I_D=1mA

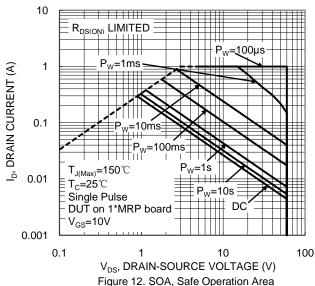




0.6

V_{SD}, SOURCE-DRAIN VOLTAGE (V) Figure 9. Diode Forward Voltage vs. Current

0.9





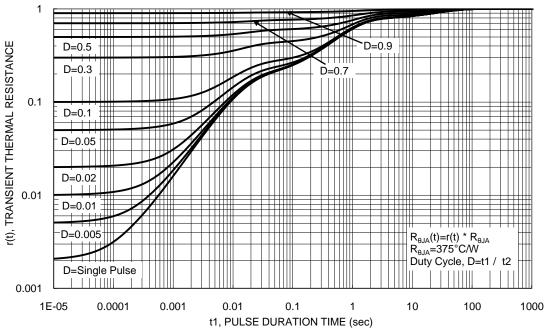


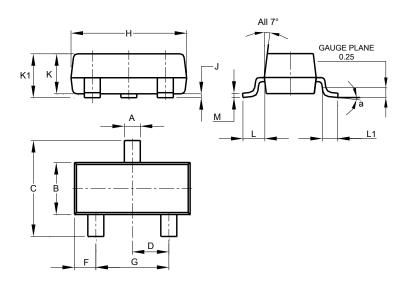
Figure 13. Transient Thermal Resistance



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23

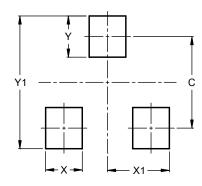


SOT23							
Dim	Min	Max	Тур				
Α	0.37	0.51	0.40				
В	1.20	1.40	1.30				
C	2.30	2.50	2.40				
D	0.89	1.03	0.915				
F	0.45	0.60	0.535				
G	1.78	2.05	1.83				
Η	2.80	3.00	2.90				
7	0.013	0.10	0.05				
K	0.890	1.00	0.975				
K 1	0.903	1.10	1.025				
٦	0.45	0.61	0.55				
L1	0.25	0.55	0.40				
М	0.085	0.150	0.110				
а	0°	8°					
All Dimensions in mm							

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23



Dimensions	Value (in mm)
С	2.0
Х	0.8
X1	1.35
Y	0.9
V1	2.0



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